

# Nanostructured thermoelectric generators

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Providing a sustainable supply of energy to the world's population will become a major societal problem for the 21<sup>st</sup> century. Thermoelectric materials, whose combination of thermal, electrical, and semiconducting properties, allows them to convert waste heat into electricity, are expected to play an increasingly important role in meeting the energy challenge of the future. Recent work on the theory of thermoelectric devices has led to the expectation that their performance could be enhanced if the diameter of the wires could be reduced to a point where quantum confinement effects increase charge-carrier mobility (thereby increasing the Seebeck coefficient) and reduce thermal conductivity. The predicted net effect of reducing diameters to the order of tens of nanometers would be to increase efficiency or ZT index by a factor of 3.

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Its main objective is to investigate and optimize nanostructures influencing ZT in order to achieve a power conversion efficiency >20%. For that, nanowire arrays of state of art n and p-type semiconductor materials will be prepared by cost-effective mass-production electrochemical methods and fabricate devices with a ZT >2 for applications in energy scavenging and as cooler/heating devices. Three lines of research are followed:

- determination of the best materials for each temperature range (n and p type) optimizing composition, microstructure, shapes (core/shell nanowires, surface texture, heterostructures), interfaces and orientations,
- advanced characterization, device development and modeling will be used iteratively during nanostructures and materials optimization, and
- nano-engineering less conventional thermoelectric like "cage compounds" by electrodeposition methods.

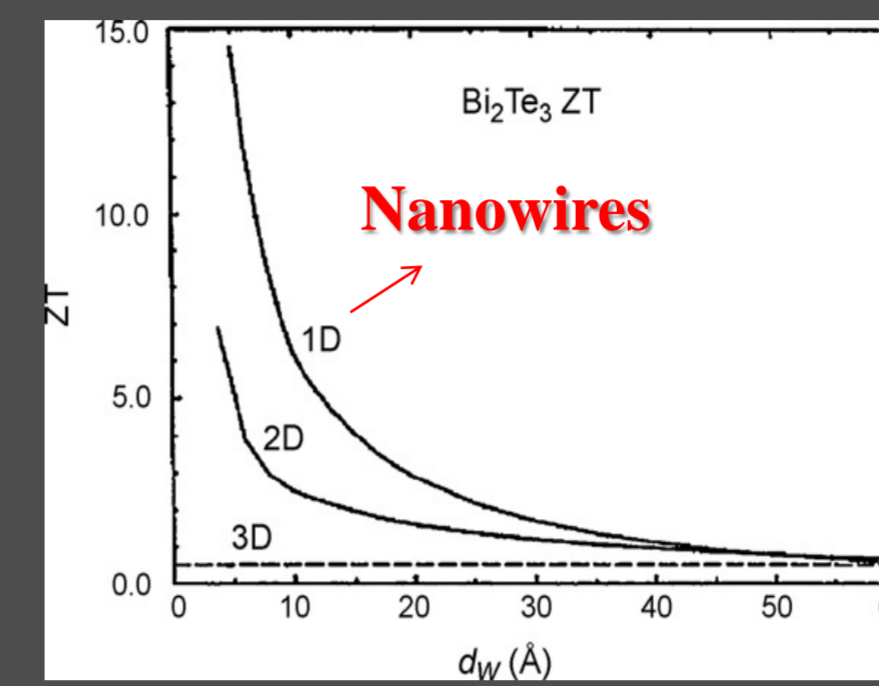
## Theory of Low-dimensional Thermoelectrics

$$ZT = \frac{S^2 \sigma}{\kappa} T$$

Effects of reduced dimensionality

- Increase in S
  - quantum confinement effect
- Decrease in  $\kappa$ 
  - introduction of interphases

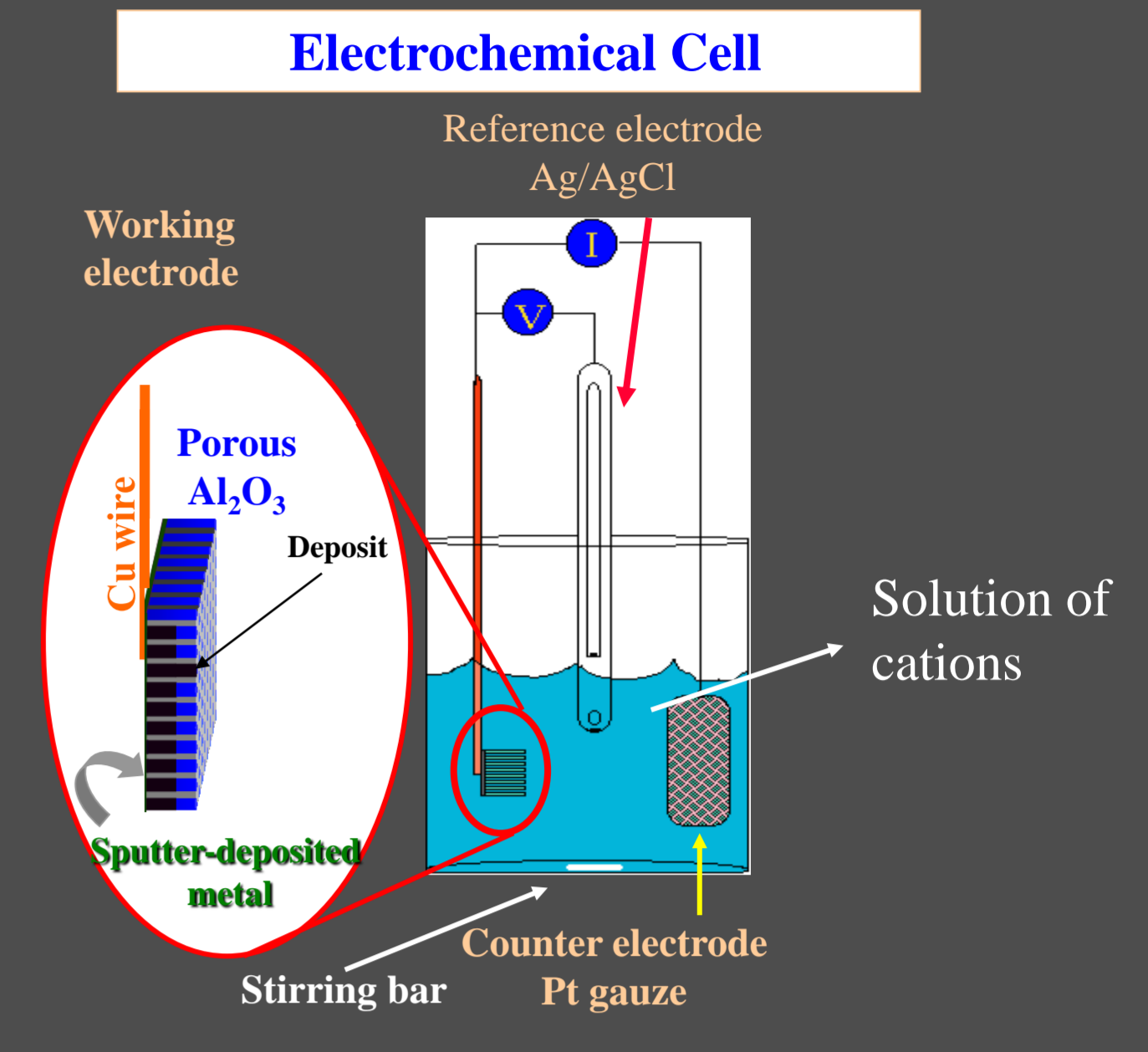
Theoretical investigation



Dependence of  $Z_{2D}T$  and  $Z_{1D}T$  on quantum-well and quantum-wire widths  $d_{qw}$  for bismuth  
From L.D. Hicks & M.S. Dresselhaus, MIT

Low dimensionality should improve the properties of thermoelectric materials

## Fabrication of Nanowires by electrodeposition



## Nanowire Arrays

### Why?

- Commercially used ZT~1 at 300K

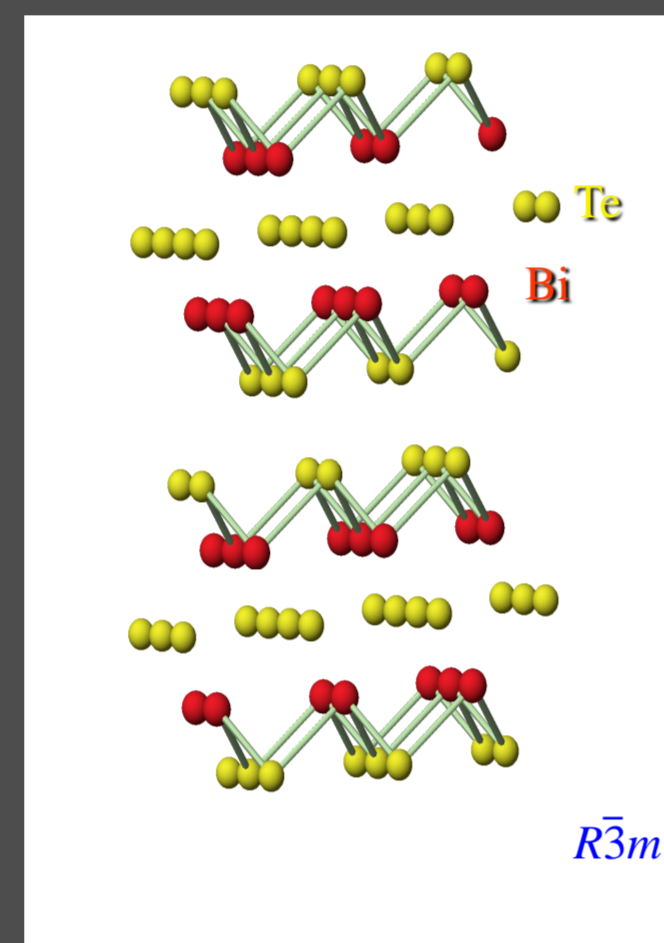


$S \approx -240 \mu V/K$   
 $\sigma \approx 10 \mu\Omega \cdot m$   
 $\kappa \approx 2.02 W/m \cdot K$

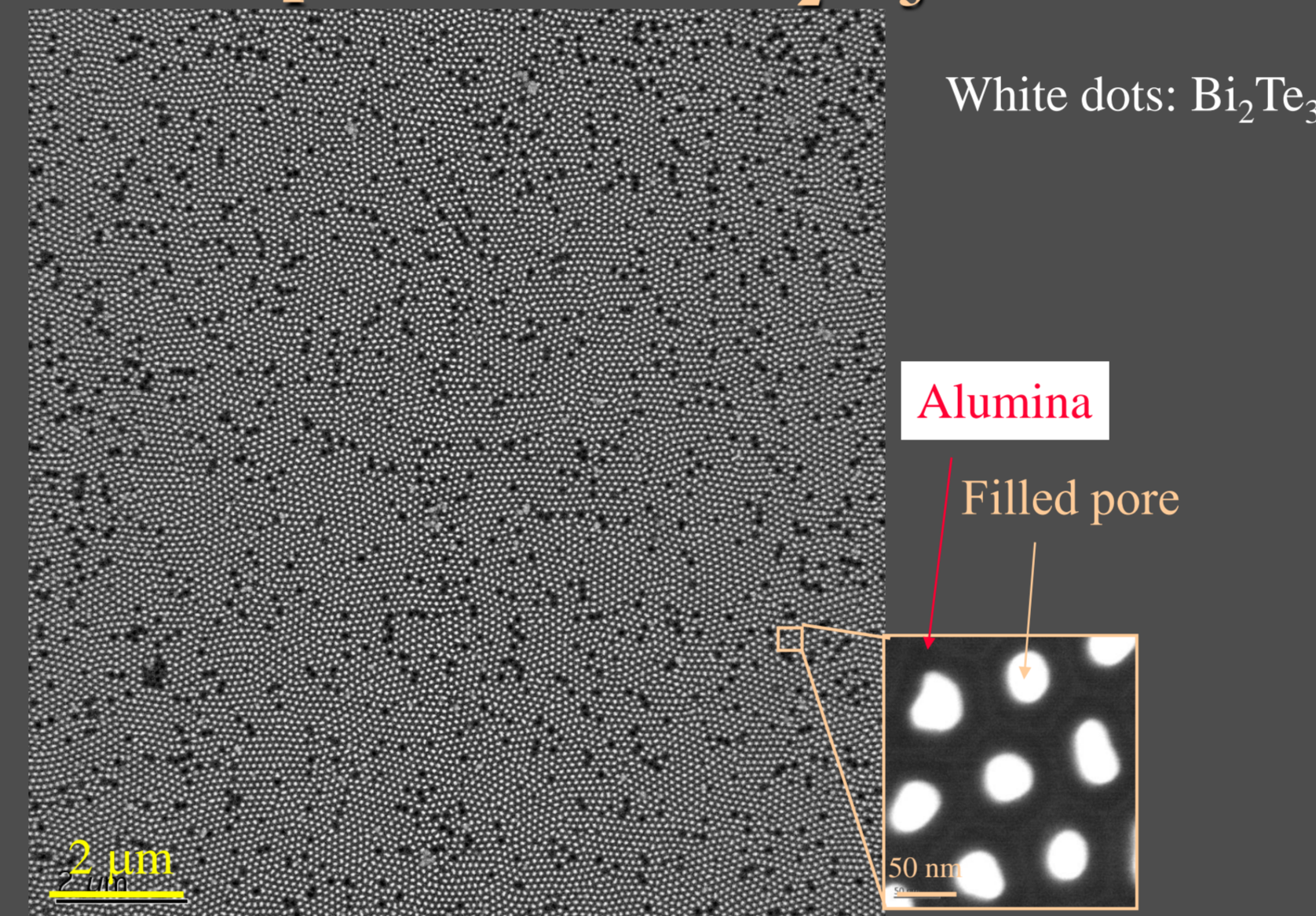
- It can be electrodeposit (Takahashi *et al.*, 1993)

- Anisotropy

### Structure



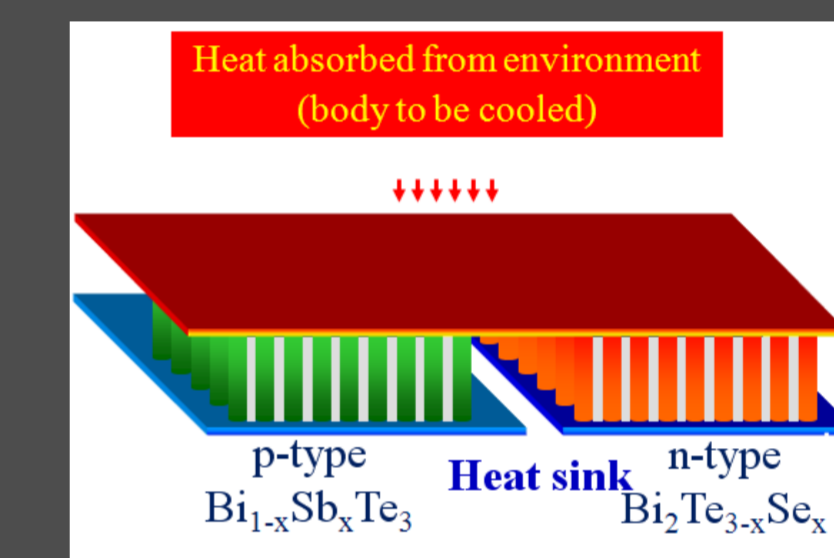
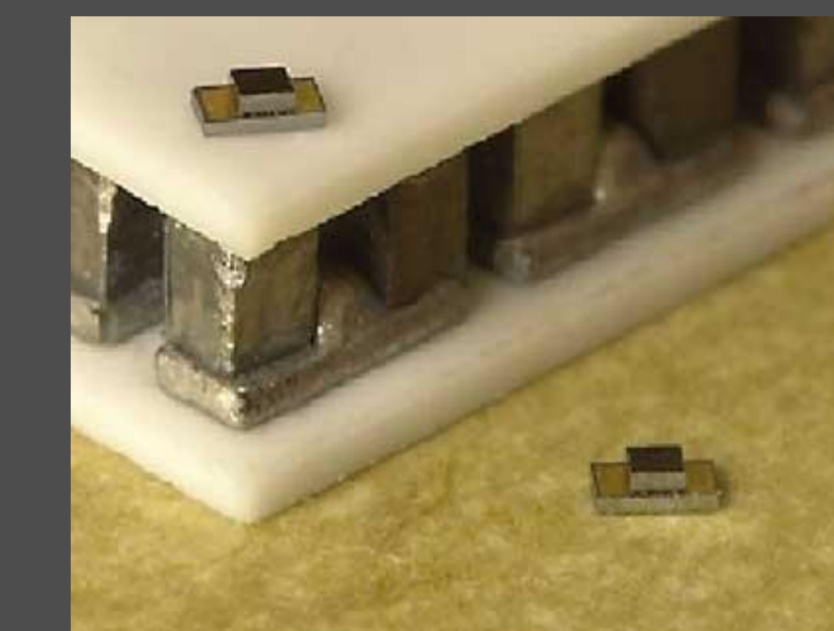
## FE-SEM top view 50 nm Bi<sub>2</sub>Te<sub>3</sub> nanowire



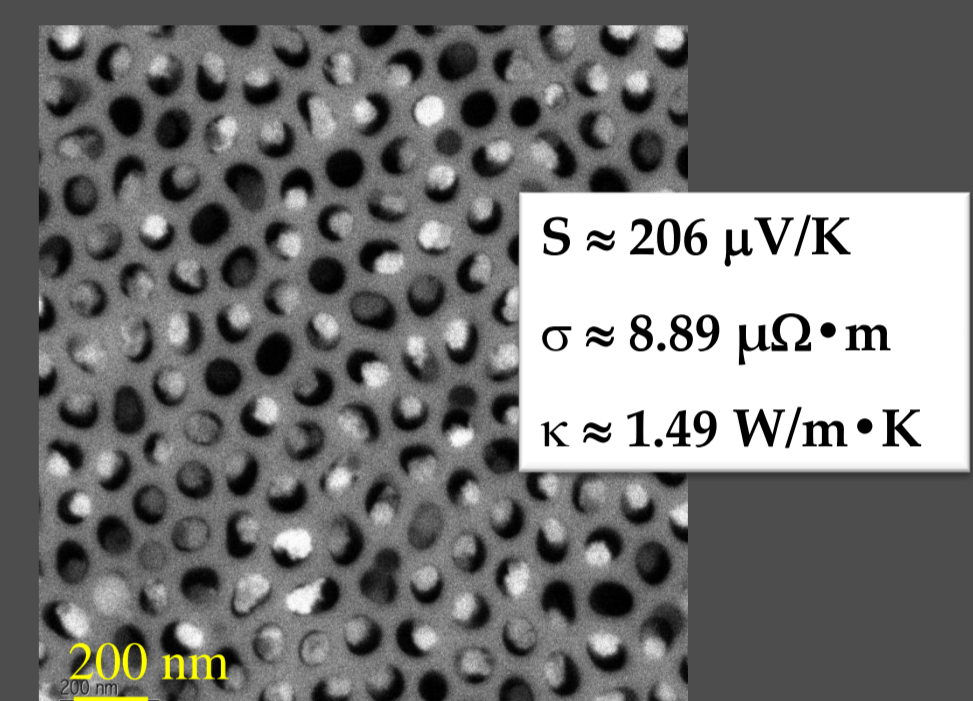
Well ordered, >90% Nucleation

Bi<sub>2</sub>Te<sub>3</sub> wires fill the pores completely → wetting effect

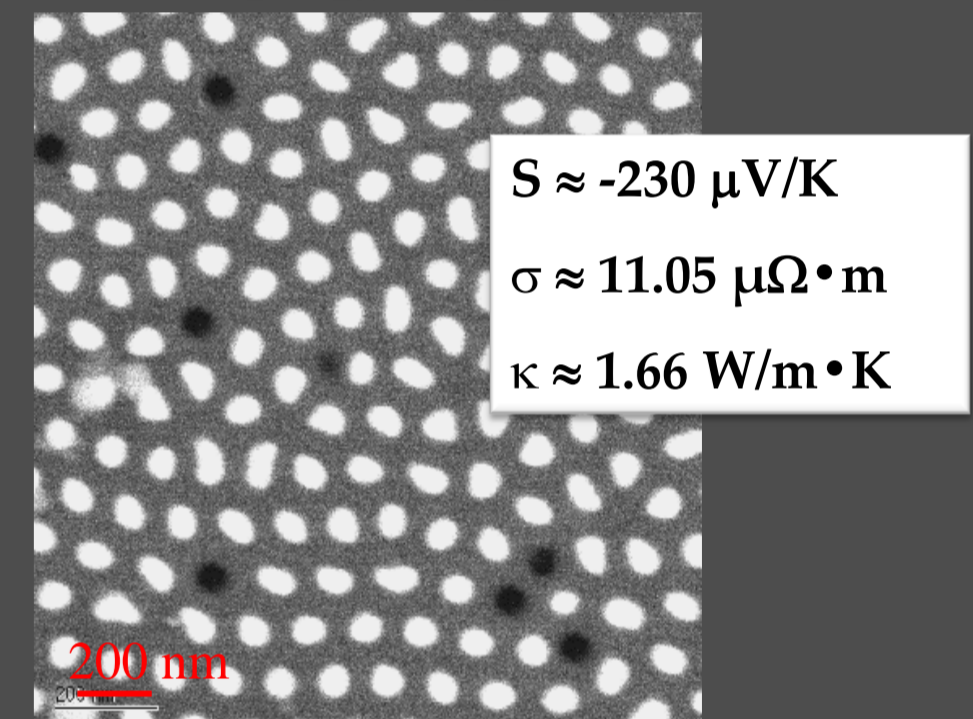
Thin film Peltier element.



50 nm Bi<sub>0.7</sub>Sb<sub>1.4</sub>Te<sub>2.9</sub> wire array



50 nm Bi<sub>2</sub>Te<sub>2.7</sub>Se<sub>0.2</sub> wire array



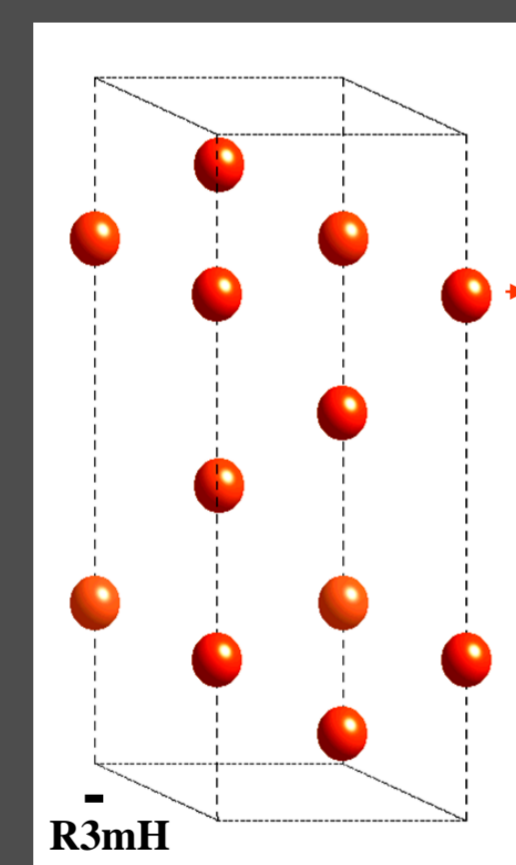
### Why?

- Solid solution
- Best low temperature thermoelectric ZT ~ 0.88 at 12% Sb and 80K

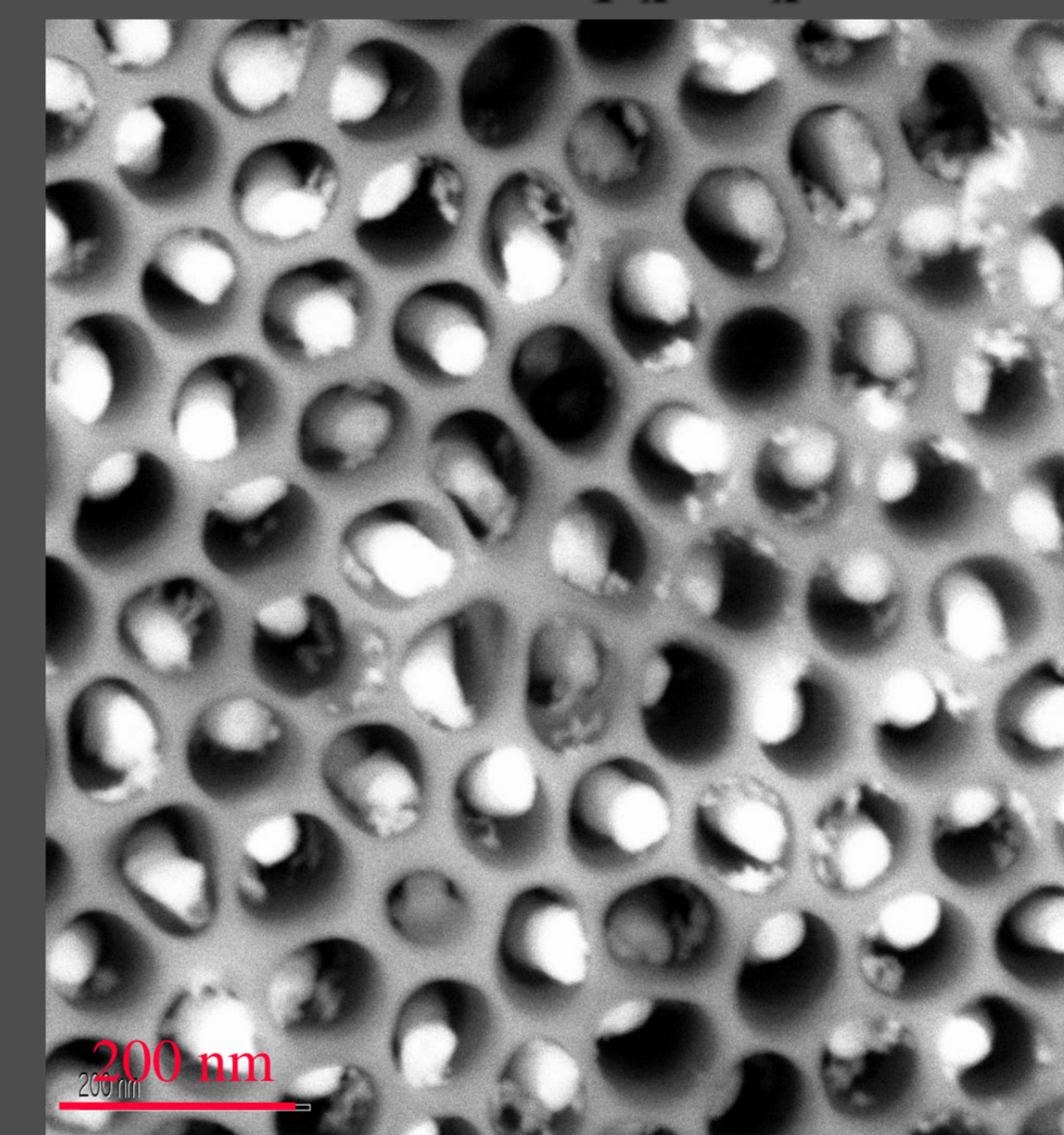
$S \approx -160 \mu V/K$   
 $\sigma \approx 1.5 \mu\Omega \cdot m$   
 $\kappa \approx 2.4 W/m \cdot K$

- Calculations by Dresselhaus *et al.* suggest a ZT ~ 1.25-1.5, diameters of ~40 nm, x ~0.13

### Structure

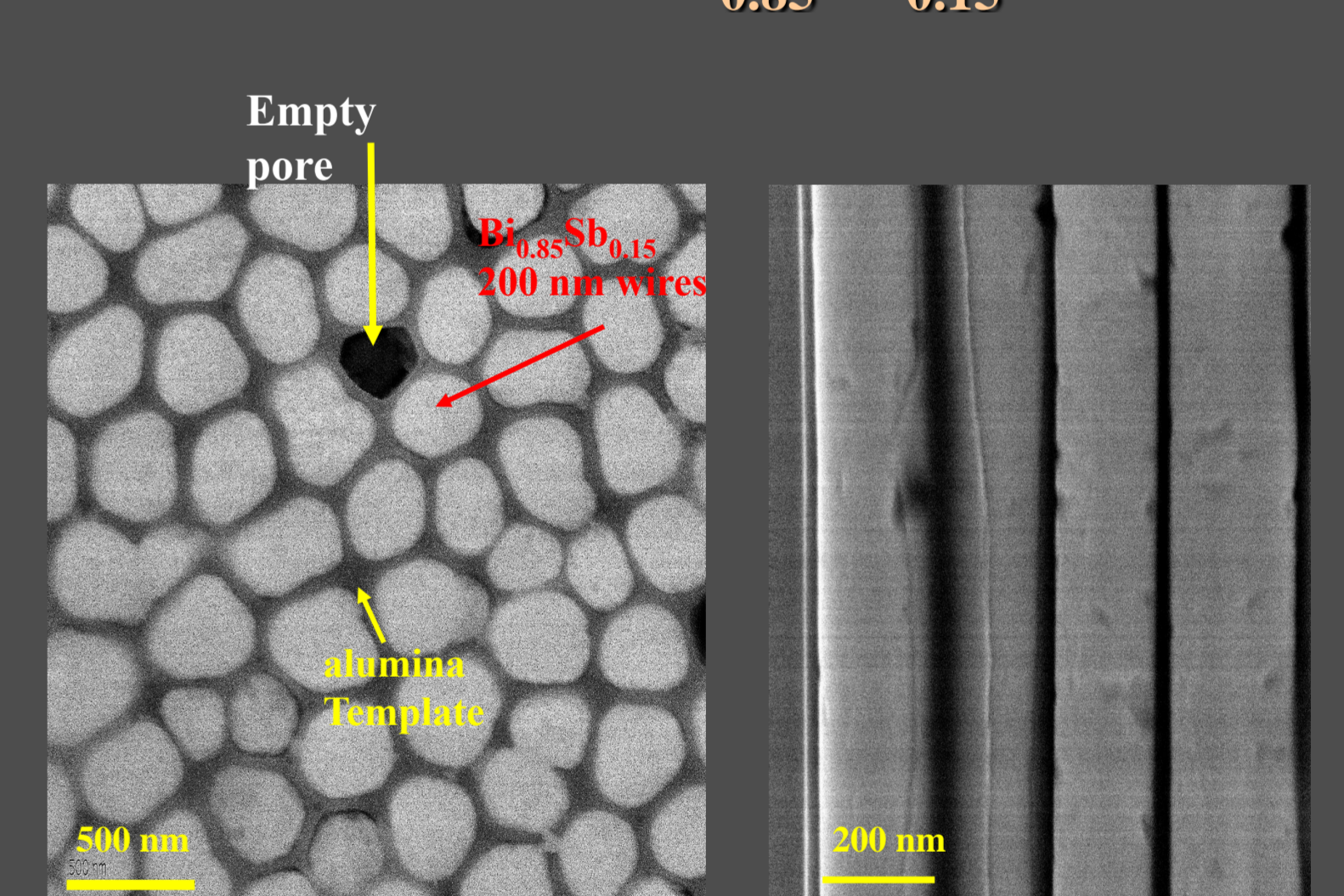


## FE-SEM 40 nm Bi<sub>1-x</sub>Sb<sub>x</sub> nanowire array



- The wire diameter is smaller than the pore diameter
- The wire grows concentrically in the pore but does not wet the alumina walls

## FE-SEM of 200 nm Bi<sub>0.85</sub>Sb<sub>0.15</sub> nanowires



- The pores can be filled by doing the process more slowly but non wetting effects are still observed

### Why?

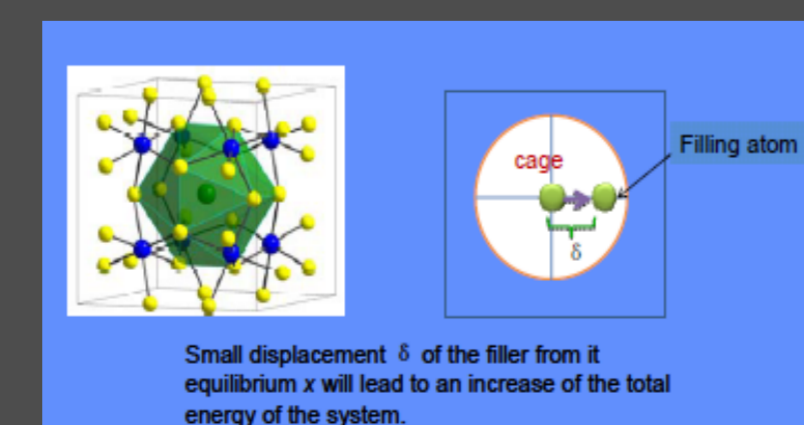
- Part of the Skutterudite (CoAs<sub>3</sub>) family
- ZT ≈ 1.47 at 573K



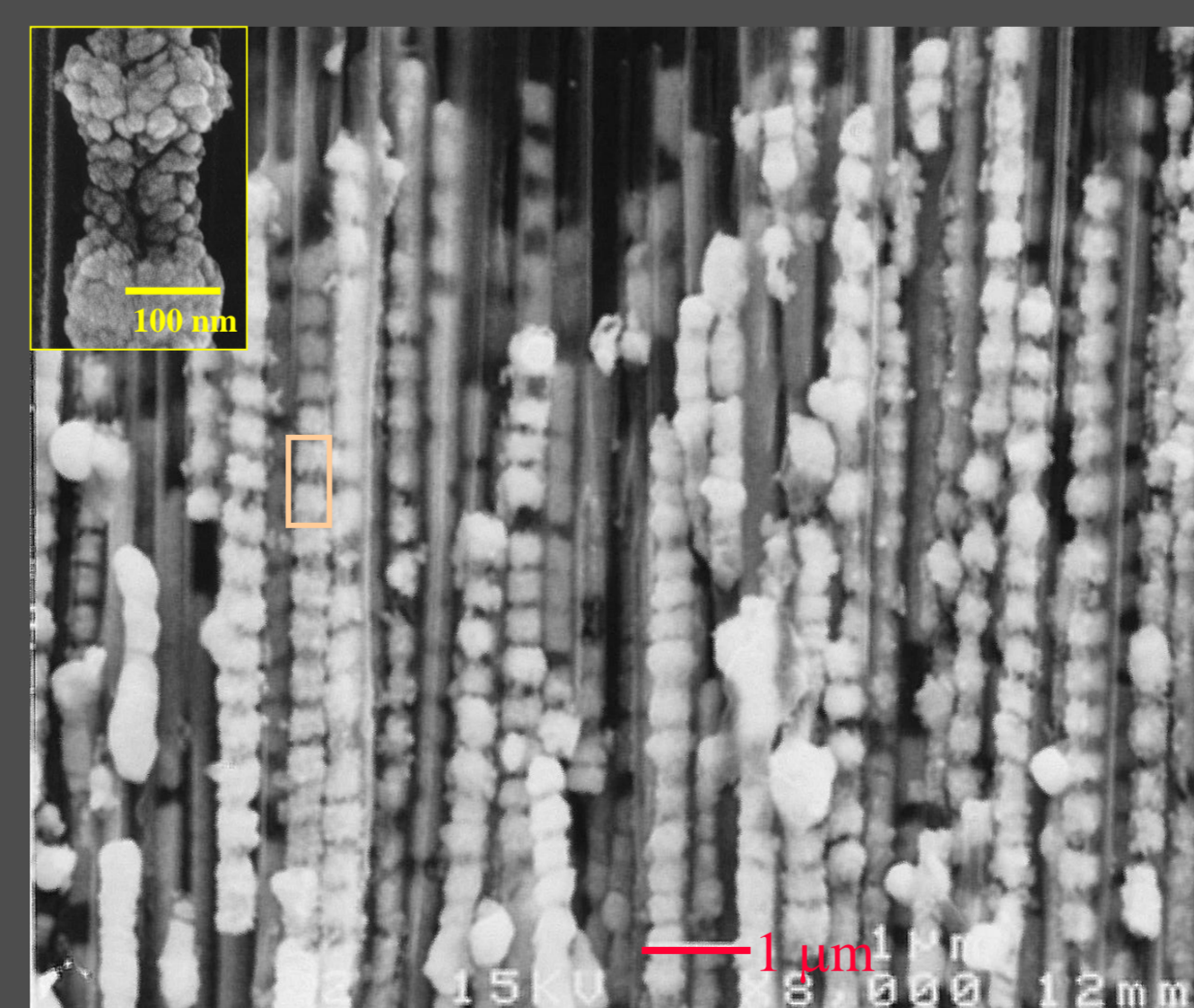
$S \approx 220 \mu V/K$   
 $\sigma \approx 10 \mu\Omega \cdot m$   
 $\kappa \approx 3.2 W/m \cdot K$

- Separation:
  - electronic structure
  - thermal conductivity
- Isotropic

## Rattler type Structure



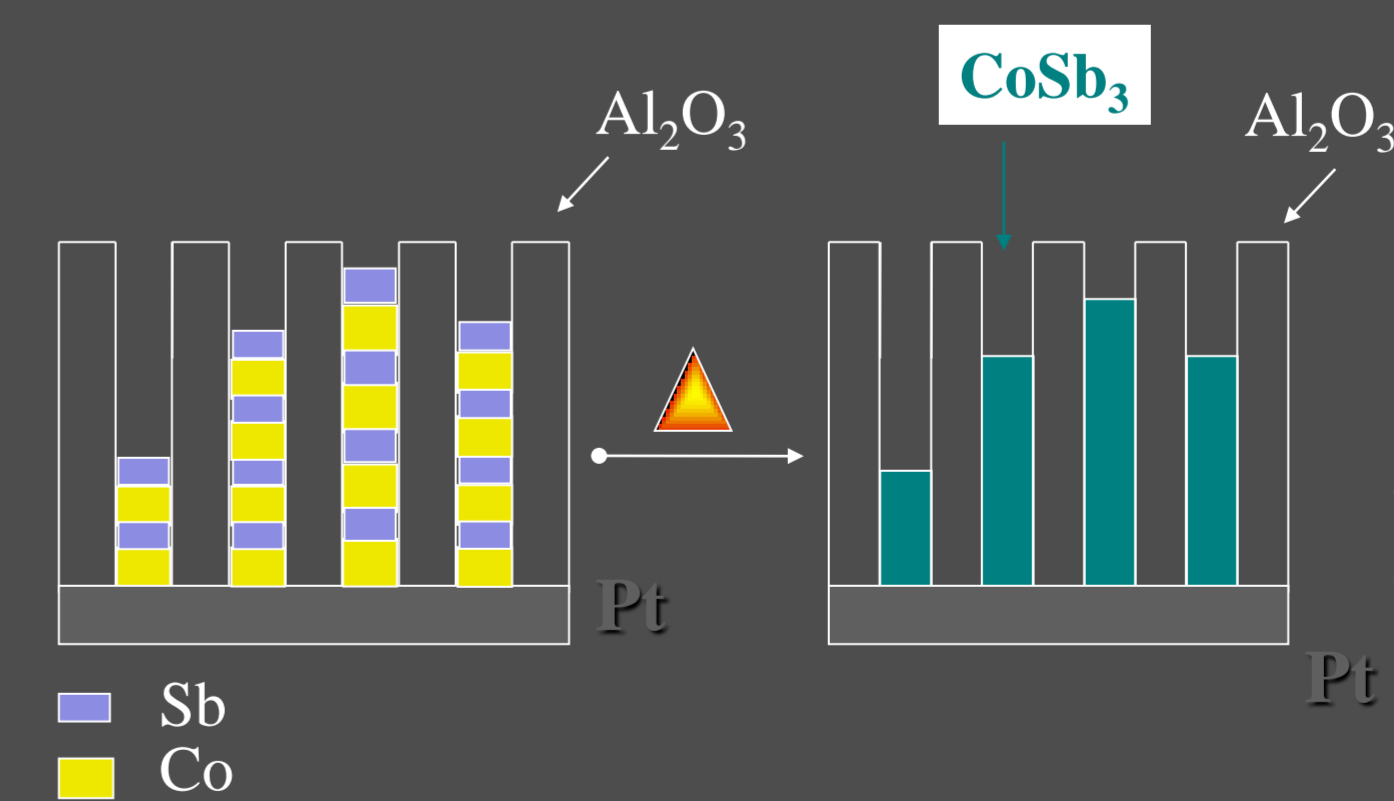
## CoSb<sub>3</sub>: Post-annealed Morphology



- Co layer wet alumina walls while Sb layer do not.
- There is also a reduction in volume after heating.
- All that gives a very interesting periodic constriction along the length of the wire

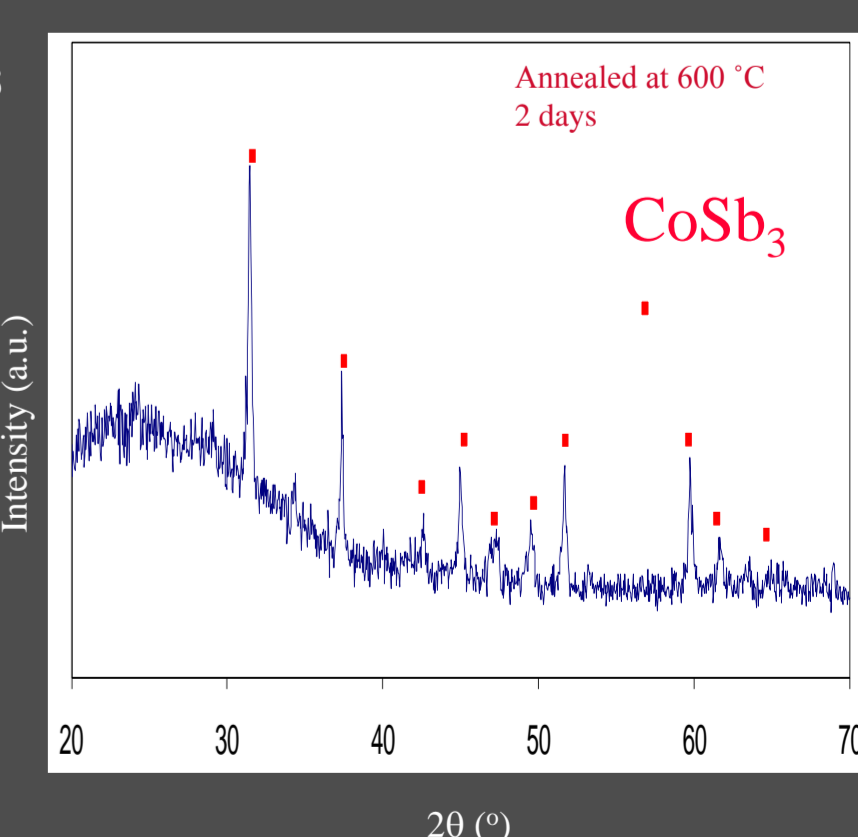
## CoSb<sub>3</sub>: Electrodeposition sequence

Multilayer deposition into 200 nm Al<sub>2</sub>O<sub>3</sub> templates



Deposition: 8 to 30 multilayers, 50°C

XRD



## Conclusions:

➤ Nanowire arrays of thermoelectric materials like Bi<sub>2</sub>Te<sub>3</sub>, Bi<sub>2-x</sub>Sb<sub>x</sub>Te<sub>3</sub>, Bi<sub>2</sub>Te<sub>3-x</sub>Se<sub>x</sub>, Bi<sub>1-x</sub>Sb<sub>x</sub> and CoSb<sub>3</sub> have been successfully prepared.

➤ Because of the "wetting/non-wetting" effects between the porous alumina and the material inside the pore different and technologically interesting nanostructures can be found!!!!

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